

Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.8)	V_{pp}	1	kV

NOTE 1: Operating junction temperature T_j is up to 125 when a resistor 1k is connected between Gate and Cathode. Without this resistor, the T_j is up to 110 only.

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33$	-	40	200	μA A D

100-8

MARKING

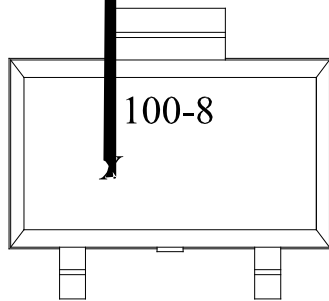


FIG.5: On-state characteristics

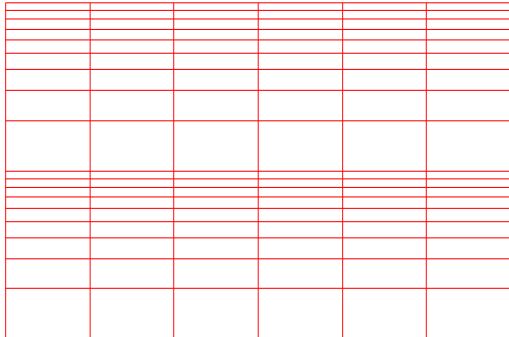
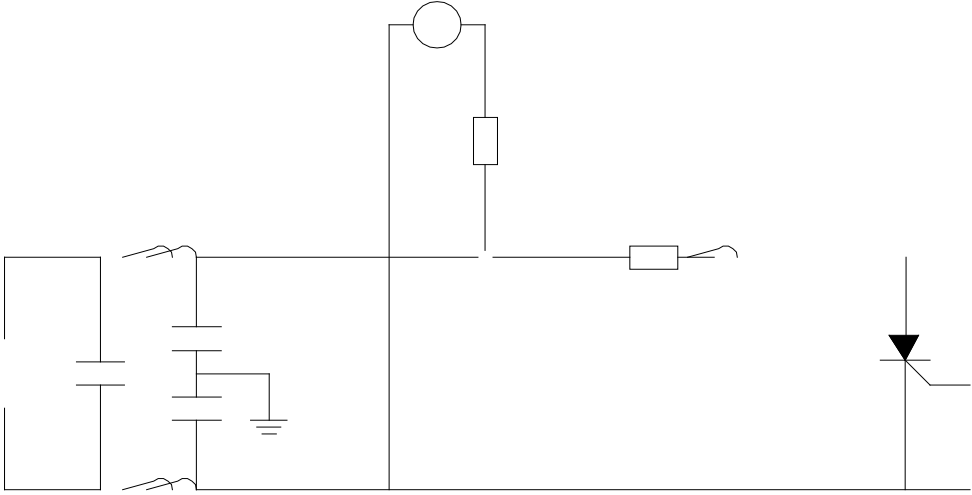


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($dI/dt < 100\text{A}/\mu\text{s}$)

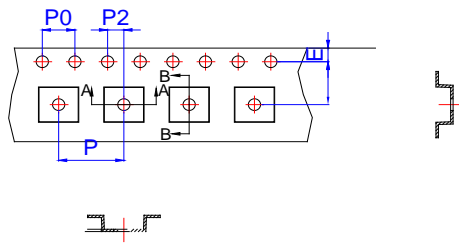
FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION


Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT \$	Package	Base qty. (pcs)	DeliveryD <input type="text"/>
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DELIVERY MODE



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
P2	1.90	2.00	2.10	0.075	0.079	0.082
D	-	1.50	1.60	-	0.059	0.063
D1	1.50			0.059		
P0	3.90	4.00	4.10	0.154	0.157	0.161
10P0	39.80	40.00	40.20	1.567	1.575	1.583
W			12.30			0.482
P	7.90	8.00	8.10	0.311	0.315	0.319
A0	5.20	5.30	5.40	0.204	0.208	0.212
B0	4.80	4.90	5.00	0.188	0.192	0.196
K0	1.75	1.85	1.95	0.069	0.073	0.076
t	0.20	0.25	0.30	0.008	0.010	0.012
	3°		5°	3°		5°

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